

# C2D20120D-Silicon Carbide Schottky Diode

# ZERO RECOVERY® RECTIFIER

 $\mathbf{V}_{\mathsf{RRM}} = 1200 \ \mathsf{V}$ 

 $I_{E} = 20 A$ 

 $Q_c = 122 \text{ nC}$ 

#### **Features**

- 1200-Volt Schottky Rectifier
- Zero Reverse Recovery
- Zero Forward Recovery
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Swtitching
- Positive Temperature Coefficient on V<sub>E</sub>

#### **Benefits**

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

# PIN 10 PIN 20 CASE PIN 30

**Package** 

TO-247-3

#### **Applications**

- Switch Mode Power Supplies
- Power Factor Correction
- Motor Drives

Part Number	Package	Marking	
C2D20120D	TO-247-3	C2D20120	

#### **Maximum Ratings**

Symbol	Parameter	Value	Unit	Test Conditions	Note
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage		V		
V <sub>RSM</sub>	Surge Peak Reverse Voltage	1200	V		
V <sub>DC</sub>	DC Blocking Voltage		V		
$I_{F(AVG)}$	Average Forward Current (Per Leg/Device)		А	T <sub>c</sub> =150°C T <sub>c</sub> =125°C	
$I_{\text{F(PEAK)}}$	Peak Forward Current (Per Leg/Device)		А	T <sub>c</sub> =125°C, T <sub>REP</sub> <1 mS, Duty=0.5	
$\mathrm{I}_{FRM}$	Repetitive Peak Forward Surge Current	50*	А	$T_c=25$ °C, $t_p=8.3$ ms, Half Sine Wave	
$I_{FSM}$	Non-Repetitive Peak Forward Surge Current	250*	А	$T_c=25$ °C, $t_p=10$ µs, Pulse	
P <sub>tot</sub>	Power Dissipation (Per Leg)		W	T <sub>c</sub> =25°C T <sub>c</sub> =125°C	
T <sub>J</sub> , T <sub>stg</sub>	Operating Junction and Storage Temperature	-55 to +175	°C		
	TO-247 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	

<sup>\*\*</sup> Per Device, \* Per Leg



#### **Electrical Characteristics (Per Leg)**

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V <sub>F</sub>	Forward Voltage	1.6 2.5	1.8 3.0	V	$I_F = 10 \text{ A } T_J = 25^{\circ}\text{C}$ $I_F = 10 \text{ A } T_J = 175^{\circ}\text{C}$	
I <sub>R</sub>	Reverse Current	10 20	200 1000	μΑ	$V_R = 1200 \text{ V } T_J = 25^{\circ}\text{C}$ $V_R = 1200 \text{ V } T_J = 175^{\circ}\text{C}$	
Q <sub>c</sub>	Total Capacitive Charge	61		nC	$V_{R} = 1200 \text{ V, } I_{F} = 10\text{A}$ $di/dt = 500 \text{ A/}\mu\text{s}$ $T_{J} = 25^{\circ}\text{C}$	
С	Total Capacitance	1000 80 59		pF	$V_R = 0 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 200 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1$ MHz $V_R = 400 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1$ MHz	

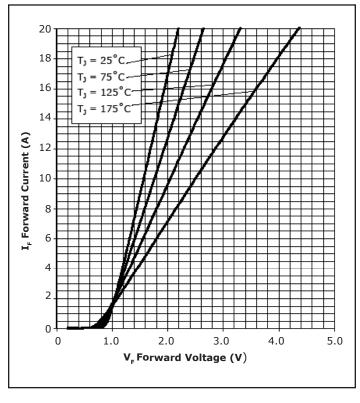
#### Note:

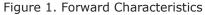
#### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
$R_{_{ heta JC}}$	Thermal Resistance from Junction to Case	0.48** 0.24*		°C/W		

<sup>\*\*</sup> Per Leg, \* Both Legs

### **Typical Performance (Per Leg)**





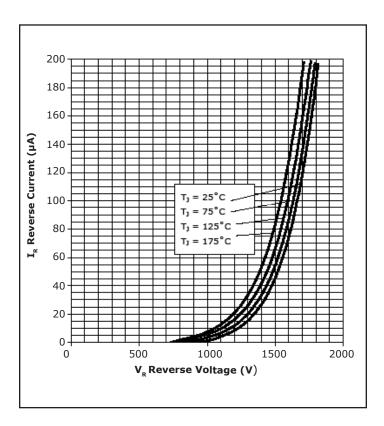
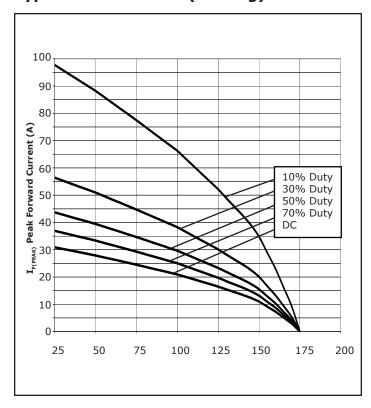


Figure 2. Reverse Characteristics

<sup>1.</sup> This is a majority carrier diode, so there is no reverse recovery charge.



#### **Typical Performance (Per Leg)**



800 700 600 (pF) 500 Capacitance 400 300 O 200 100 0 -100 1000 10 1 V<sub>R</sub> Reverse Voltage (V)

Figure 3. Current Derating

Figure 4. Capacitance vs. Reverse Voltage

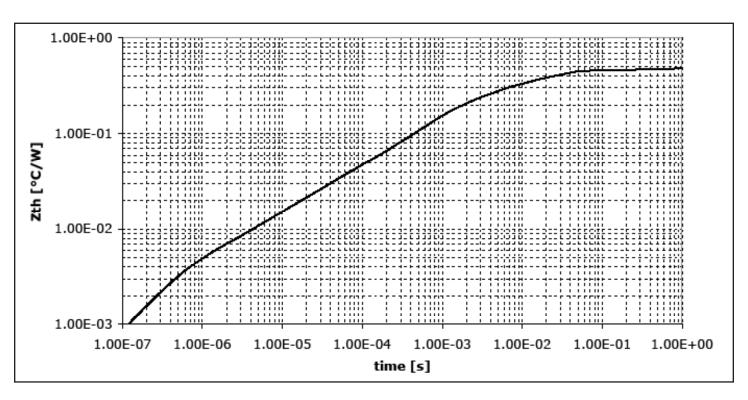
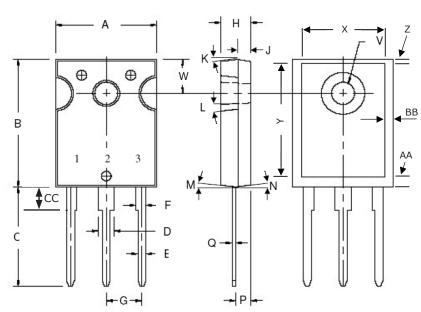


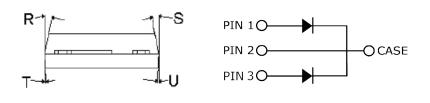
Figure 5. Transient Thermal Impedance



## **Package Dimensions**

Package TO-247-3

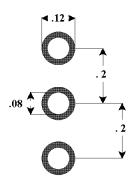




POS		hes	Millimeters		
PUS	Min	Min Max		Max	
Α	.605	.631	15.367	16.027	
В	.800	.830	20.320	21.082	
С	.789	.800	20.05	20.31	
D	.095	.126	2.413	3.200	
Е	.046	.052	1.168	1.321	
F	.060	.084	1.524	2.134	
G	.215	TYP	.215 TYP		
Н	.180	.203	4.572	5.156	
J	.078	.081	1.982	2.057	
К	6°	21°	6°	21°	
L	4°	6°	4°	6°	
М	2°	4°	2°	4°	
N	2°	4°	2°	4°	
Р	.090	.097	2.286	2.464	
Q	.020	.030	.508	.762	
R	9°	11°	9°	11°	
S	9°	11°	9°	11°	
Т	2°	8°	2°	8°	
U	2°	8°	2°	8°	
V	.138	.144	3.505	3.658	
W	.210	.220	5.334	5.588	
Х	.502	.557	12.751	14.148	
Y	.637	.695	16.180	17.653	
Z	.040	.052	1.016	1.321	
AA	.032	.046	.813	1.168	
BB	.110	.140	2.794	3.556	
CC	.164	.176	4.168	4.472	



#### **Recommended Solder Pad Layout**



TO-247-3

Part Number	Package	Marking	
C2D20120D	TO-247-3	C2D20120	

"The levels of environmentally sensitive, persistent biologically toxic (PBT), persistent organic pollutants (POP), or otherwise restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2002/95/EC on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS), as amended through April 21, 2006."

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, air traffic control systems, or weapons systems.

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